

ZXMP3A17DN8

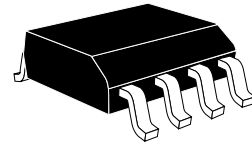
DUAL P-CHANNEL 30V ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -30V$; $R_{DS(ON)} = 0.070\Omega$; $I_D = -4.4A$

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



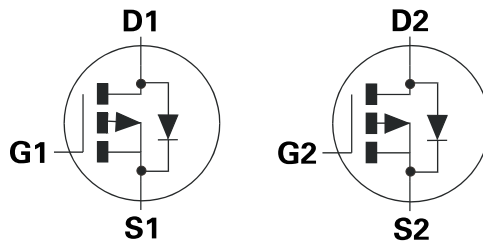
SO8

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- Motor Drive
- LCD backlighting



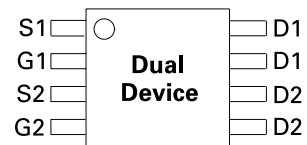
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A17DN8TA	7"	12mm	500 units
ZXMP3A17DN8TC	13"	12mm	2500 units

DEVICE MARKING

ZXMP
3A17D

PINOUT



Top view

ZXMP3A17DN8

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current @ $V_{GS}=10V$; $T_A=25^\circ C$ (b)(d) @ $V_{GS}=10V$; $T_A=70^\circ C$ (b)(d) @ $V_{GS}=10V$; $T_A=25^\circ C$ (a)(d)	I_D	-4.4 -3.6 -3.4	A A A
Pulsed Drain Current (c)	I_{DM}	-16.2	A
Continuous Source Current (Body Diode)(b)	I_S	-2.5	A
Pulsed Source Current (Body Diode)(c)	I_{SM}	-16.2	A
Power Dissipation at $T_A=25^\circ C$ (a)(d) Linear Derating Factor	P_D	1.25 10	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (a)(e) Linear Derating Factor	P_D	1.8 14	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b)(d) Linear Derating Factor	P_D	2.1 17	W mW/ $^\circ C$
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150	$^\circ C$

THERMAL RESISTANCE

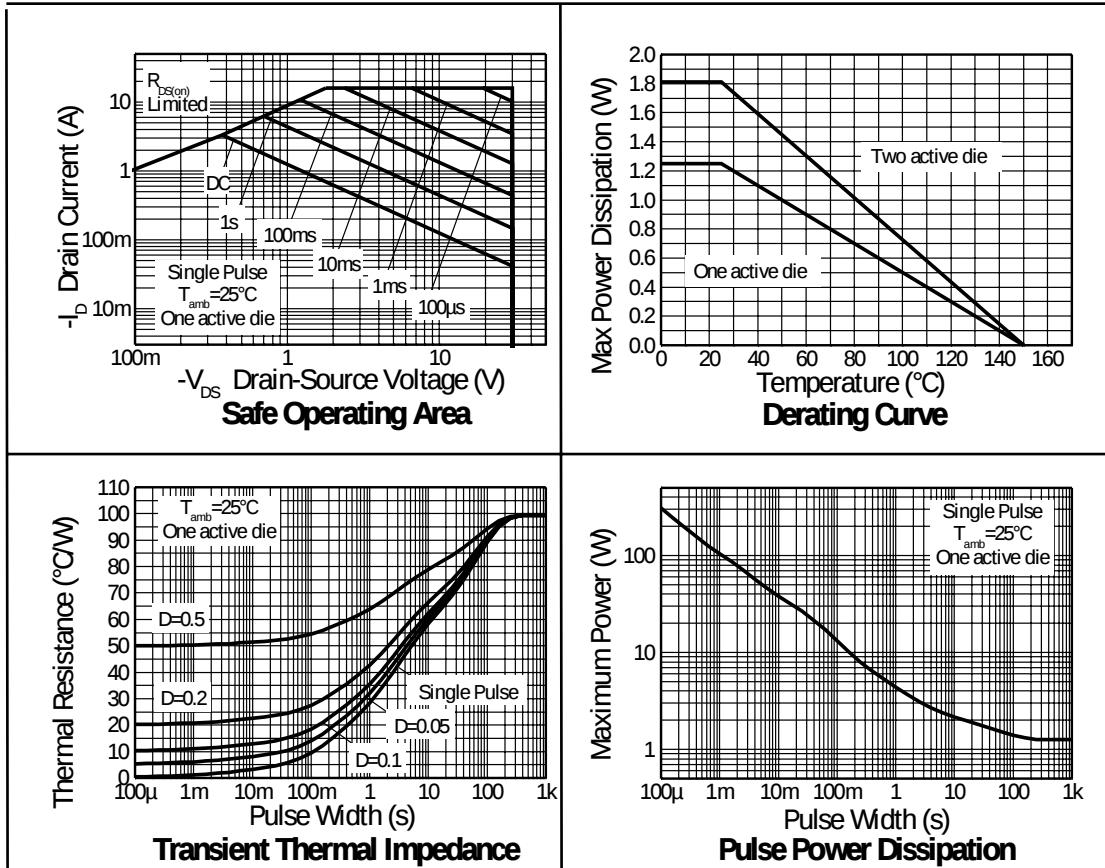
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(d)	$R_{\theta JA}$	100	$^\circ C/W$
Junction to Ambient (b)(e)	$R_{\theta JA}$	70	$^\circ C/W$
Junction to Ambient (b)(d)	$R_{\theta JA}$	60	$^\circ C/W$

Notes

- (a) For a dual device surface mounted on 25mm x 25mm FR4 PCB with coverage of single sided 1oz copper in still air conditions.
 (b) For a dual device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
 (c) Repetitive rating 25mm x 25mm FR4 PCB, $D=0.05$ pulse width= $10\mu s$ - pulse width limited by maximum junction temperature.
 (d) For a dual device with one active die.
 (e) For dual device with 2 active die running at equal power.

ZXMP3A17DN8

CHARACTERISTICS



ZXMP3A17DN8

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-30			V	I _D =-250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μA	V _{DS} =-30V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-1.0			V	I _D =-250μA, V _{DS} = V _{GS}
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.070 0.110	Ω Ω	V _{GS} =-10V, I _D =-3.2A V _{GS} =-4.5V, I _D =-2.5A
Forward Transconductance (1)(3)	g _{fs}		6.4		S	V _{DS} =-15V, I _D =-3.2A
DYNAMIC (3)						
Input Capacitance	C _{iss}		630		pF	V _{DS} =-15 V, V _{GS} =0V, f=1MHz
Output Capacitance	C _{oss}		113		pF	
Reverse Transfer Capacitance	C _{rss}		78		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	t _{d(on)}		1.74		ns	V _{DD} =-15V, I _D =-1A R _G =6.0Ω, V _{GS} =-10V
Rise Time	t _r		2.87		ns	
Turn-Off Delay Time	t _{d(off)}		29.2		ns	
Fall Time	t _f		8.72		ns	
Gate Charge	Q _g		8.28		nC	V _{DS} =-15V, V _{GS} =-5V, I _D =-3.2A
Total Gate Charge	Q _g		15.8		nC	V _{DS} =-15V, V _{GS} =-10V, I _D =-3.2A
Gate-Source Charge	Q _{gs}		1.84		nC	
Gate-Drain Charge	Q _{gd}		2.80		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V _{SD}		-0.85	-1.2	V	T _J =25°C, I _S =-2.5A, V _{GS} =0V
Reverse Recovery Time (3)	t _{rr}		19.5		ns	T _J =25°C, I _F =-1.7A, di/dt= 100A/μs
Reverse Recovery Charge (3)	Q _{rr}		16.3		nC	

NOTES

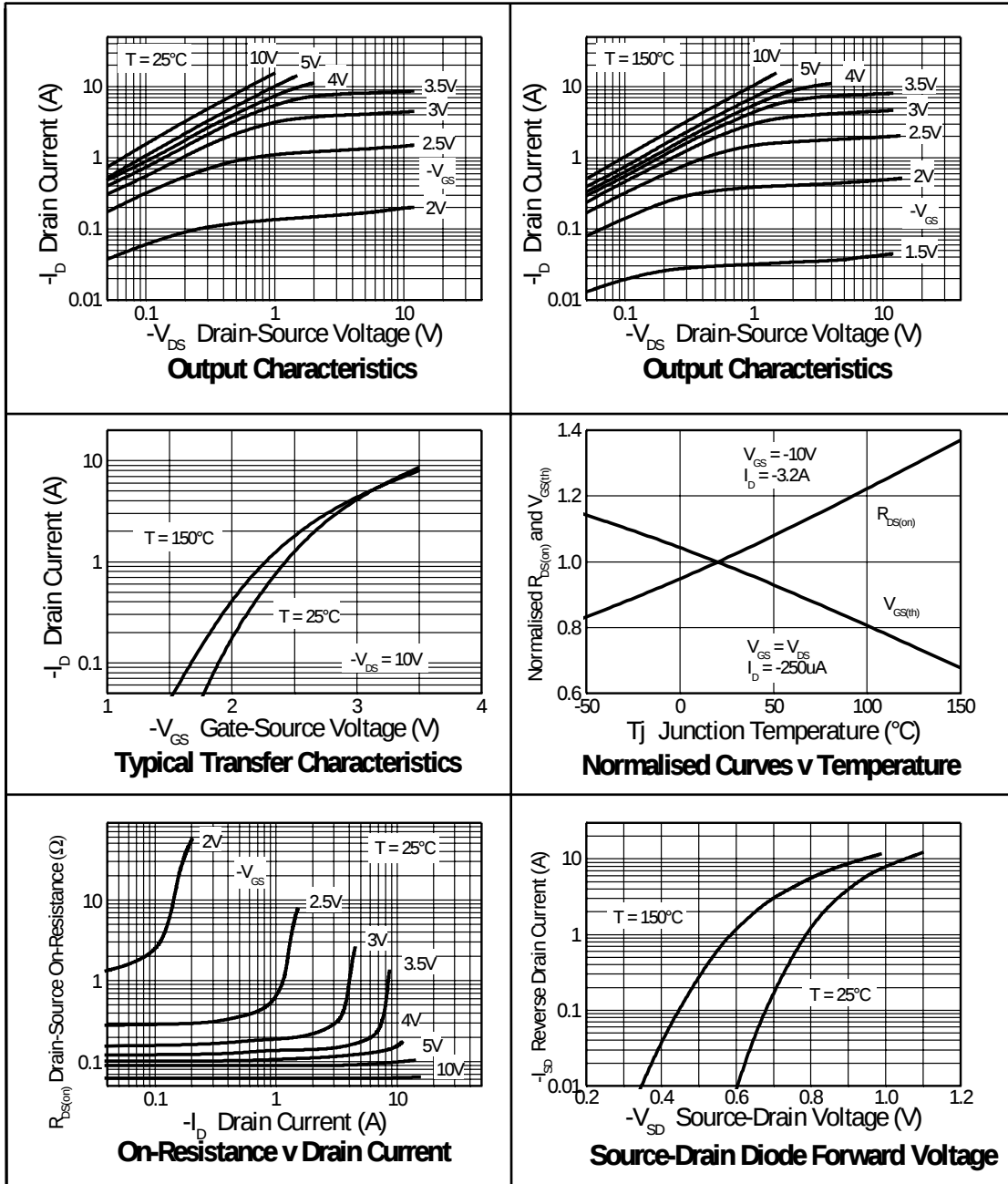
- (1) Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.



PROVISIONAL ISSUE A - AUGUST 2002

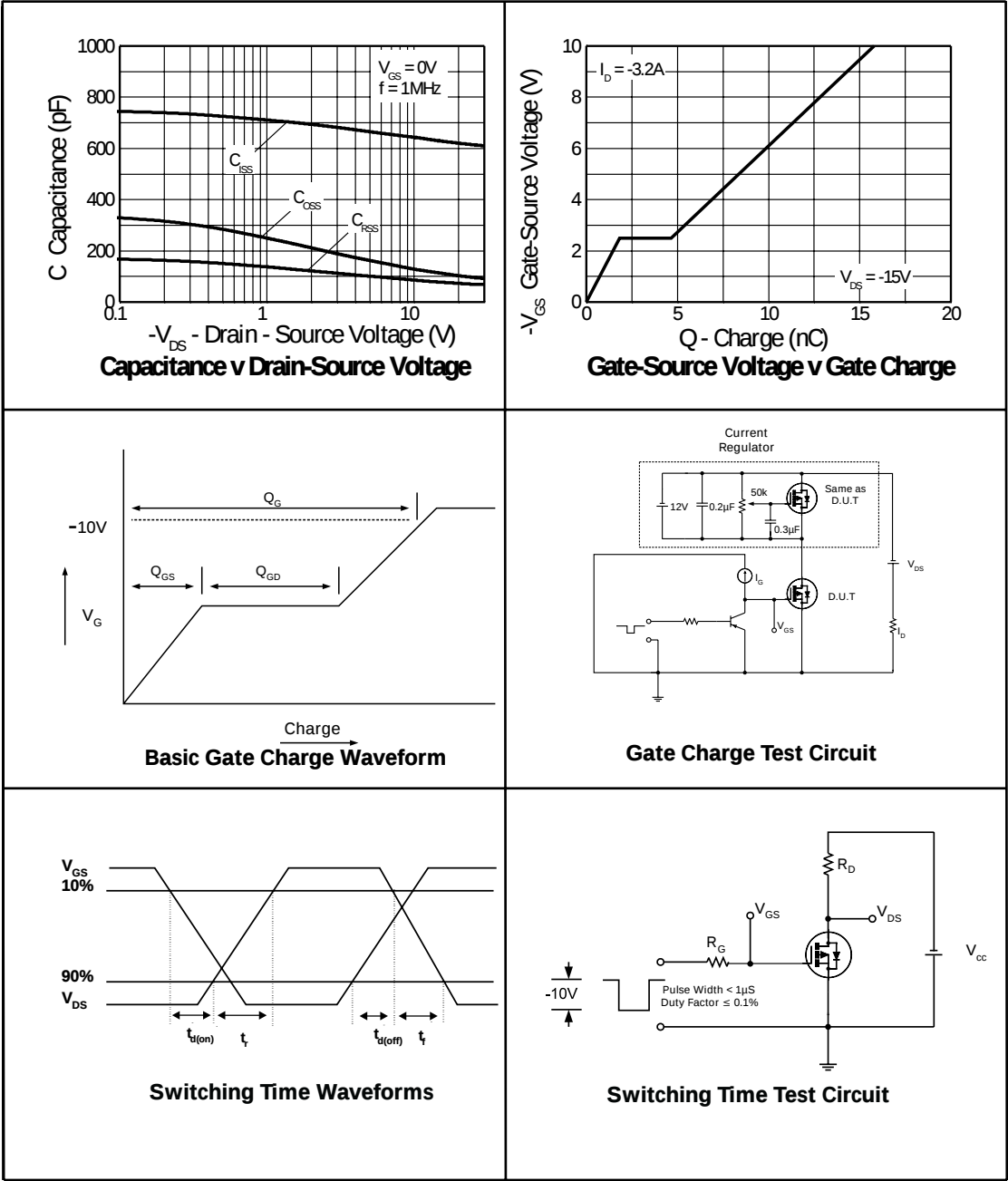
ZXMP3A17DN8

TYPICAL CHARACTERISTICS



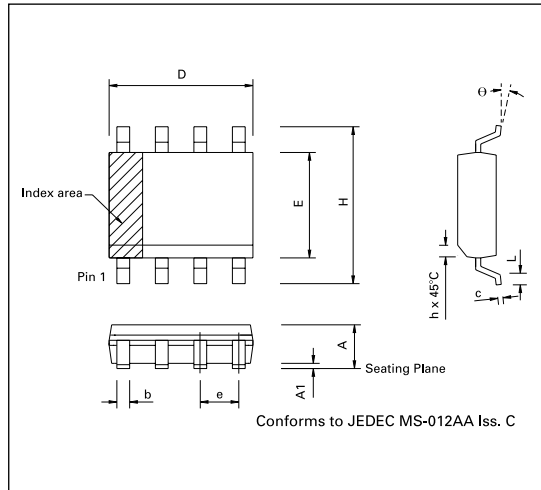
ZXMP3A17DN8

TYPICAL CHARACTERISTICS



ZXMP3A17DN8

PACKAGE OUTLINE



CONTROLLING DIMENSIONS ARE IN INCHES
APPROX IN MILLIMETRES

PACKAGE DIMENSIONS

DIM	INCHES		MILLIMETRES	
	MIN	MAX	MIN	MAX
A	0.053	0.069	1.35	1.75
A1	0.004	0.010	0.10	0.25
D	0.189	0.197	4.80	5.00
H	0.228	0.244	5.80	6.20
E	0.150	0.157	3.80	4.00
L	0.016	0.050	0.40	1.27
e	0.050 BSC		1.27 BSC	
b	0.013	0.020	0.33	0.51
c	0.008	0.010	0.19	0.25
Θ	0°	8°	0°	8°
h	0.010	0.020	0.25	0.50

© Zetex plc 2002

Europe		Americas	Asia Pacific
Zetex plc Fields New Road Chadderton Oldham, OL9 8NP United Kingdom Telephone (44) 161 622 4422 Fax: (44) 161 622 4420 uk.sales@zetex.com	Zetex GmbH Streitfeldstraße 19 D-81673 München Germany Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY11788 USA Telephone: (631) 360 2222 Fax: (631) 360 8222 usa.sales@zetex.com	Zetex (Asia) Ltd 3701-04 Metroplaza, Tower 1 Hing Fong Road Kwai Fong Hong Kong Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to **www.zetex.com**

PROVISIONAL ISSUE A - AUGUST 2002

